New Product

Vishay Siliconix

P-Channel 60-V (D-S) MOSFET

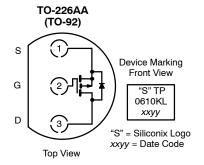
PRODUCT SUMMARY							
V _{(BR)DSS(min)} (V)	$r_{DS(on)}$ (Ω)	V _{GS(th)} (V)	I _D (A)				
-60	6 @ V _{GS} = -10 V	−1 to −3.0	-0.27				
	10 @ V _{GS} = -4.5 V	-110-3.0	-0.21				

FEATURES

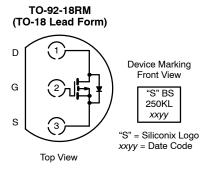
TrenchFET® Power MOSFET
ESD Protected: 2000 V

APPLICATIONS

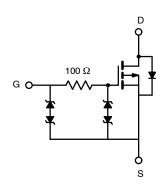
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- Battery Operated Systems
- Power Supply, Converter Circuits
- Motor Control







Ordering Information: BS250KL-TR1



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter		Symbol	Limit	Unit			
Drain-Source Voltage		V_{DS}	-60	.,			
Gate-Source Voltage		V _{GS}	±20	٧			
Continuous Drain Current	T _A = 25°C		-0.27				
	T _A = 70°C	I _D	-0.22	Α			
Pulse Drain Current ^a		I _{DM}	-1.0				
Power Dissipation	T _A = 25°C	PD	0.8	w			
	T _A = 70°C	טי	0.51	VV			
Maximum Junction-to-Ambient		R _{thJA}	156	°C/W			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	°C			

Notes

a. Pulse width limited by maximum junction temperature.

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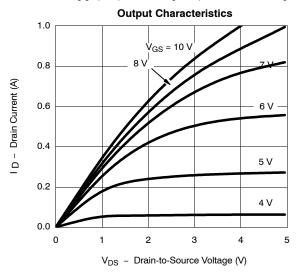
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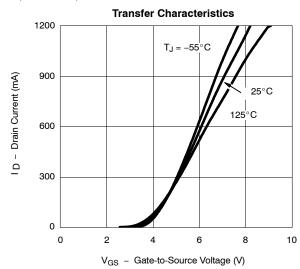


SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Test Condition	Min	Тур	Max	Unit	
Static							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_{D} = -10 \mu A$	-60			V	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$	-1	-2.1	-3.0	1	
Gate-Body Leakage		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±10	μΑ	
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}$			±200	nA	
	IGSS	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}, T_J = 85^{\circ}\text{C}$			±500		
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 5 \text{ V}$			±100		
Zero Gate Voltage Drain Current		$V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ	
	DSS	V_{DS} = -60 V, V_{GS} = 0 V, T_J = 55 $^{\circ}$ C			-10		
On-State Drain Current ^a		$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}$	-50			mA	
	I _{D(on)}	$V_{DS} = -10 \text{ V}, V_{GS} = -10 \text{ V}$	-600				
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = -25 \text{ mA}$		5.5	10	Ω	
		$V_{GS} = -10 \text{ V}, I_D = -500 \text{ mA}$		3.1	6		
		$V_{GS} = -10 \text{ V}, I_D = -500 \text{ mA}, T_J = 125^{\circ}\text{C}$		4.7	9		
Forward Transconductancea	9fs	$V_{DS} = -10 \text{ V}, I_D = -100 \text{ mA}$		180		mS	
Diode Forward Voltage ^a	V _{SD}	$I_S = -200 \text{ mA}, V_{GS} = 0 \text{ V}$		-0.9	-1.4	V	
Dynamic ^b							
Total Gate Charge	Qg	V_{DS} = -30 V, V_{GS} = -15 V, $I_D \cong$ -500 mA		1.7	3	nC	
Gate-Source Charge	Q _{gs}			0.26			
Gate-Drain Charge	Q _{gd}			0.46			
Gate Resistance	R _g			285		Ω	
Turn-On Time	t _{d(on)}			2.4	5	ns ns	
	t _r	$V_{DD} = -25 \text{ V}, R_L = 150 \Omega$ $I_D \cong -150 \text{ mA}, V_{GEN} = -10 \text{ V}$ $R_a = 10 \Omega$		15.5	25		
Turn-Off Time	t _{d(off)}			21	35		
	t _f	5		12.5	20		

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

For the following graphs, p-channel negative polarities for all voltage and current values are represented as positive values.





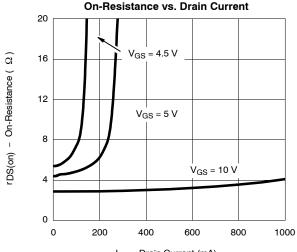
Notes
a. Pulse test: PW ≤300 ms duty cycle ≤2%.
b. Guaranteed by design, not subject to production testing.

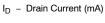


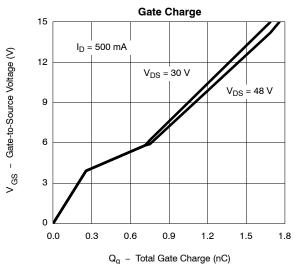
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TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

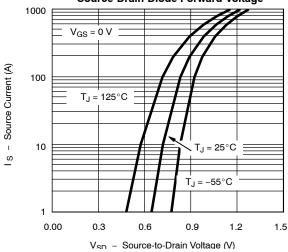
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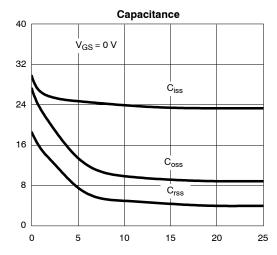




Source-Drain Diode Forward Voltage

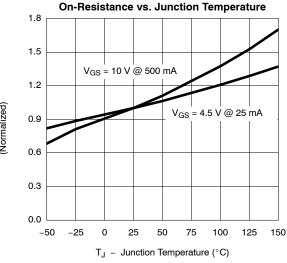


Capacitance (pF)

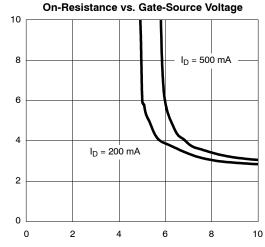


V_{DS} - Drain-to-Source Voltage (V)





8 rDS(on) – On-Resistance (Ω)



V_{GS} - Gate-to-Source Voltage (V)

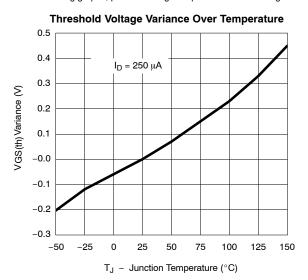
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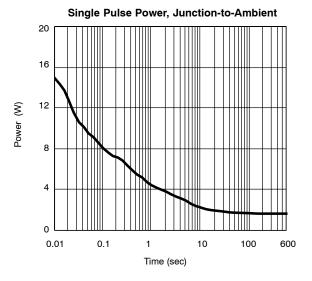
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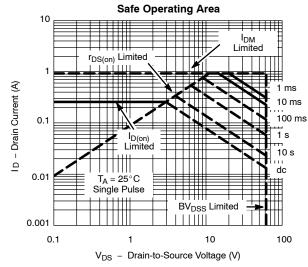


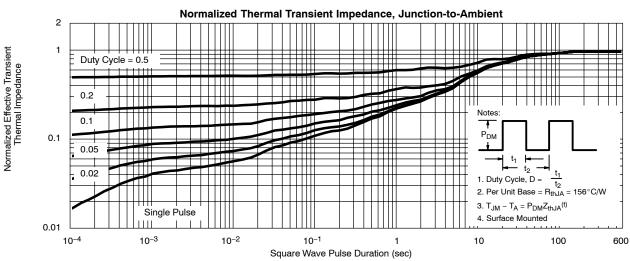
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For the following graphs, p-channel negative polarities for all voltage and current values are represented as positive values.











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